





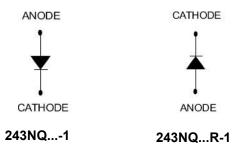
# 243NQ080/R-1 243NQ100/R-1 SCHOTTKY RECTIFIER



## **Features**

- 175℃ T<sub>J</sub> operation
- Unique high power, Half-Pak module
- Replaces three parallel DO-5'S
- Easier to mount and lower profile than DO-5' S
- High purity, high temperature epoxy encapsulation for enhanced
- · mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Baseplate: Nickel plated; Terminals: Nickel plated
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

# **Circuit Diagram**



## **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

# **Maximum Ratings:**

Characteristics	Symbol	Condition		Max.		Units	
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	-		80	243NQ080-1	V	
Working Peak Reverse Voltage DC Blocking Voltage	$V_{RWM} \ V_{R}$			100	243NQ100-1		
Average Forward Current	I <sub>F(AV)</sub>	50% duty cycle @T <sub>C</sub> =120°C, rectangular wave form			240		
		8.3 ms, half Sine pulse		3960		Α	
Maximum Peak One Cycle Non- Repetitive Surge Current	IFSM	5 us sine or 3 us rect. pulse	Following and rated load	25500		- A	
		10 ms sine or 6 ms rect. pulse	condition and with rated V <sub>RRM</sub> applied		3300		
Non-Repetitive Avalanche Energy	E <sub>AS</sub>	T <sub>J</sub> =25℃,I <sub>AS</sub> =1A,L=30 mH		15		mJ	
Repetitive Avalanche Current	I <sub>AR</sub>	Current decaying linearly to zero in 1 $\mu sec$ Frequency limited by $T_J$ max. $V_A = 1.5 \times V_R$ typical		1		А	

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# **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 240A, Pulse, T <sub>J</sub> = 25 °C	0.81	0.86	V
	$V_{F2}$	@ 240A, Pulse, T <sub>J</sub> = 125 °C	0.66	0.72	V
Reverse Current*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 25 °C	0.001	6	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 125 °C	0.5	80	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 \text{ °C}$ $f_{SIG} = 1MHz$	5423	5500	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

 $<sup>^{\</sup>star}\,$  Pulse width < 300  $\mu s,\,$  duty cycle < 2%

# **Thermal-Mechanical Specifications:**

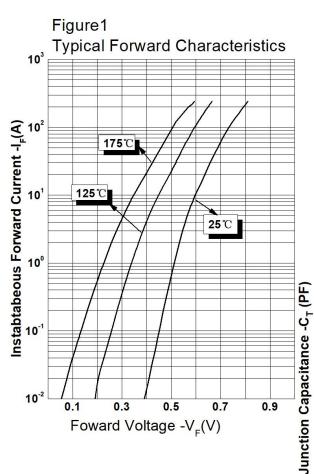
Characteristics	Symbol	Condition	Specification		Units
Junction Temperature	TJ	-	-55 to +175		°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +175		°C
Typical Thermal Resistance Junction to Case	R <sub>0</sub> JC	DC operation	0.20		°C/W
Typical Thermal Resistance, case to Heat Sink	R <sub>θcs</sub>	Mounting surface, smooth and greased	0.15		°C/W
Mounting Torque	T <sub>M</sub>	Non-lubricated threads	Mounting Torque Terminal Torque	23(min) 29(max) 35(min) 46(max)	Kg-cm
Approximate Weight	wt	-	25.6		g
Case Style	PRM1-1				

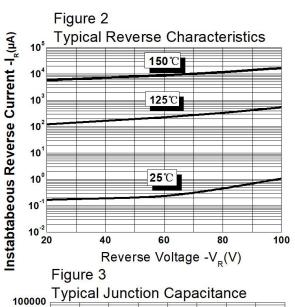


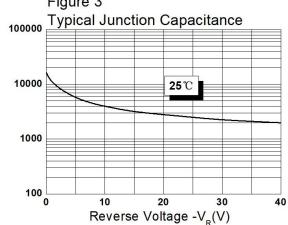




## **Ratings and Characteristics Curves**







# **Ordering Information**

Device	Package	Shipping	
243NQ SERIES	PRM1-1(Pb-Free)	27pcs/ box	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

# **Marking Diagram**



Where XXXX is YYWW

1st row SS YYWW
2nd row 243NQ080-1
SS = SS
YY = Year
WW = Week

Cautions: Molding resin

Epoxy resin UL:94V-0

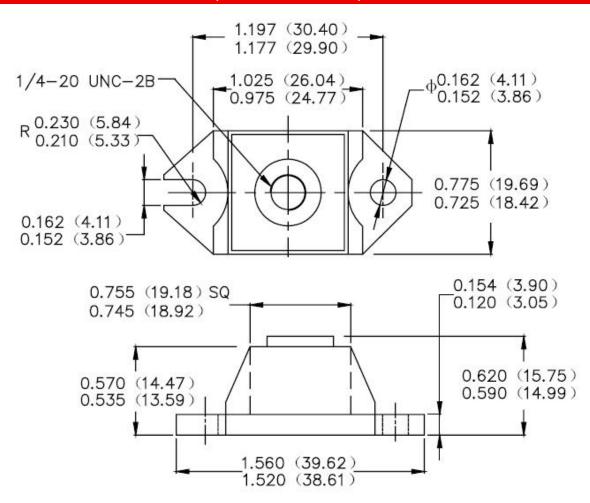
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# **Mechanical Dimensions PRM1-1 (Inches/Millimeters)**



<sup>•</sup> http://www.smc-diodes.com - sales@ smc-diodes.com •







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